Features

- Trench MV MOSFET Technology
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

P-Channel MOSFET

Maximum Ratings

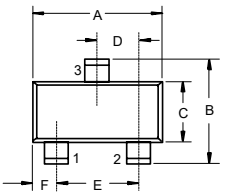
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Thermal Resistance: 162°C/W Junction to Ambient(Note2)

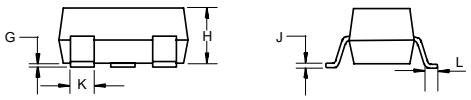
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-100	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-1	A
	T_A=100°C		-0.63	
Pulsed Drain Current(Note3)		I_{DM}	-4	A
Total Power Dissipation(Note4)		P_D	0.77	W

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

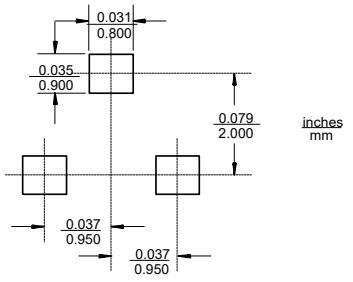
SOT-23



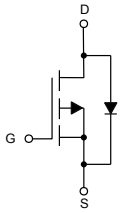


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

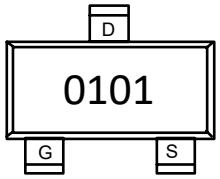
Suggested Solder Pad Layout



Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-100			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-100V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1.5	-2.2	-3.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-1.0A		560	800	mΩ
		V_{GS}=-4.5V, I_D=-0.5A		620	1000	
Gate Resistance	R_G	f=1 MHz, Open drain		4.6		Ω
Forward Tranconductance	g_{FS}	V_{DS}=-5V, I_D=-1A		5		S
Diode Characteristics						
Continuous Body Diode Current	I_S				-1	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-1A			-1.2	V
Reverse Recovery Time	t_{rr}	I_F=-1A, dI_F/dt=100A/μs		28		ns
Reverse Recovery Charge	Q_{rr}			40		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-40V,V_{GS}=0V,f=1MHz		342		pF
Output Capacitance	C_{oss}			18.3		
Reverse Transfer Capacitance	C_{rss}			14.3		
Total Gate Charge	Q_g	V_{DS}=-10V,V_{GS}=-10V,I_D=-1A		7.8		nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			0.98		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-10V, V_{GS}=-10V, R_{GEN}=2.5Ω, I_D= -1A		6.1		ns
Turn-On Rise Time	t_r			2.7		
Turn-Off Delay Time	$t_{d(off)}$			12		
Turn-Off Fall Time	t_f			3.8		

Curve Characteristics

Fig.1 - Typical Output Characteristics

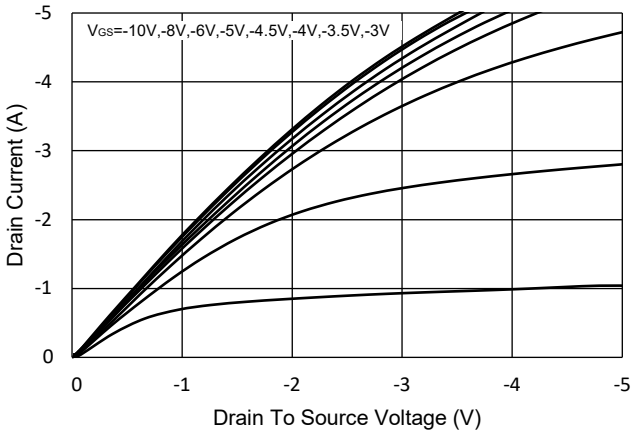


Fig.2 - Transfer Characteristic

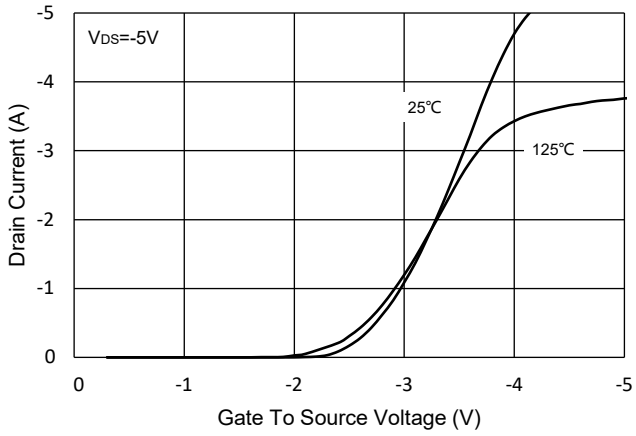


Fig.3 - $R_{DS(ON)}$ - V_{GS}

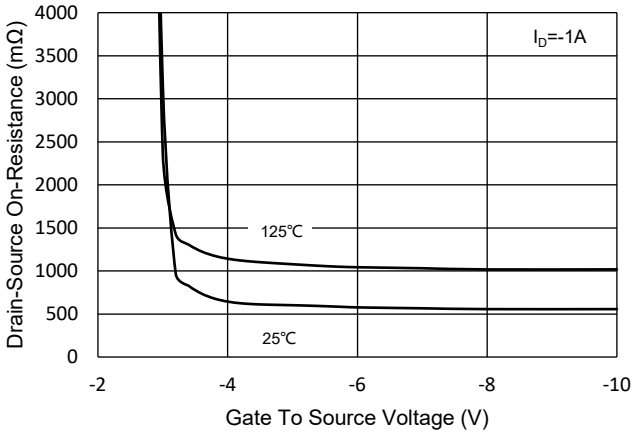


Fig.4 - $R_{DS(ON)}$ - I_D

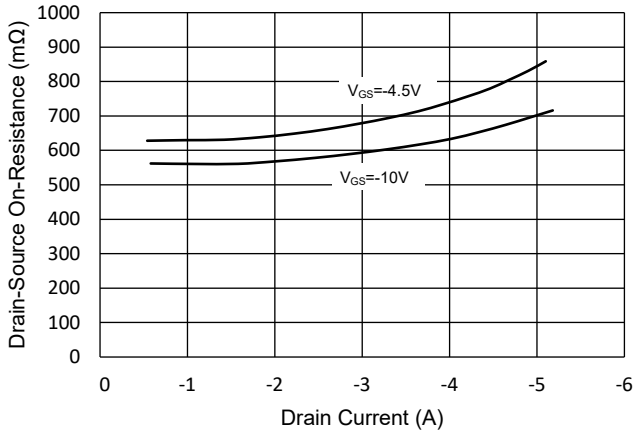


Fig.5 - Capacitance Characteristics

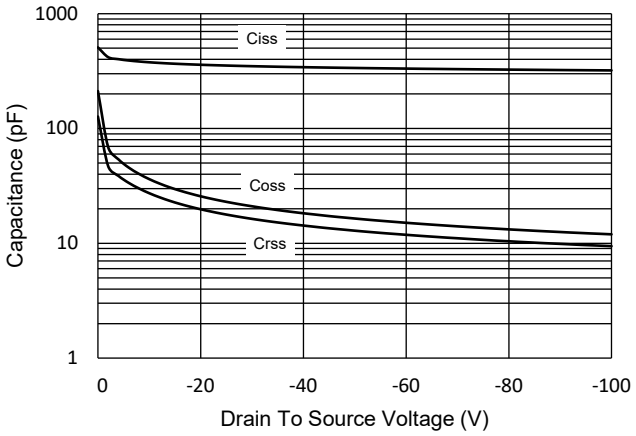
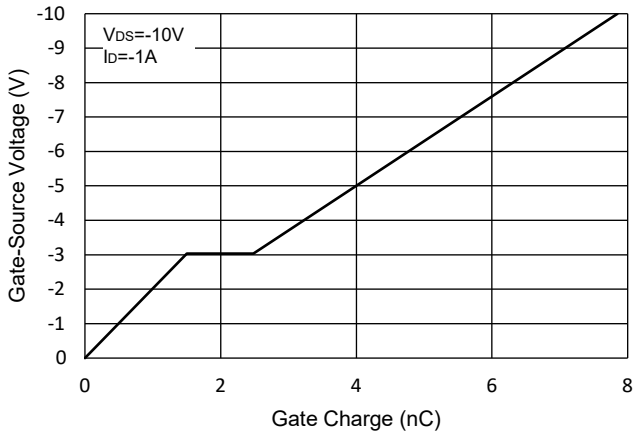


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

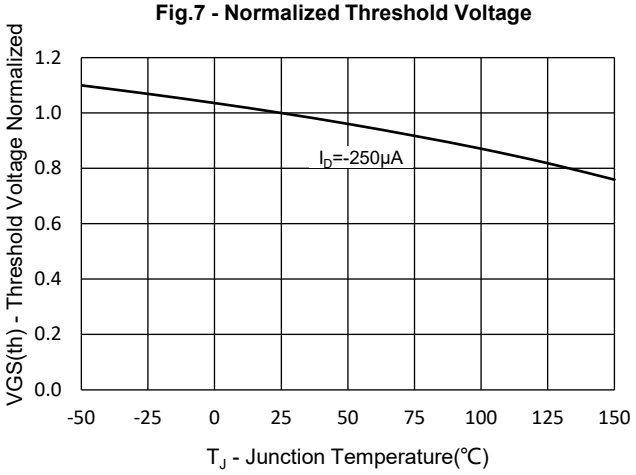


Fig.8 - Normalized On Resistance Characteristics

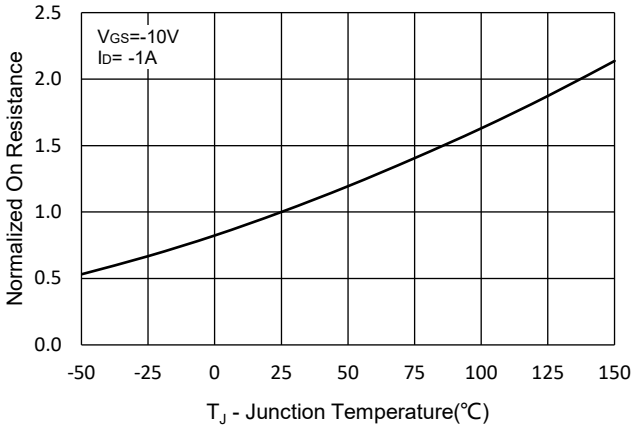


Fig.9 - I_S - V_{SD}

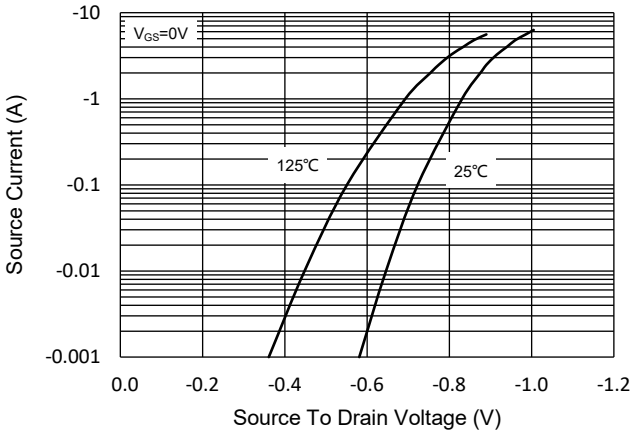


Fig.10 - Drain Current

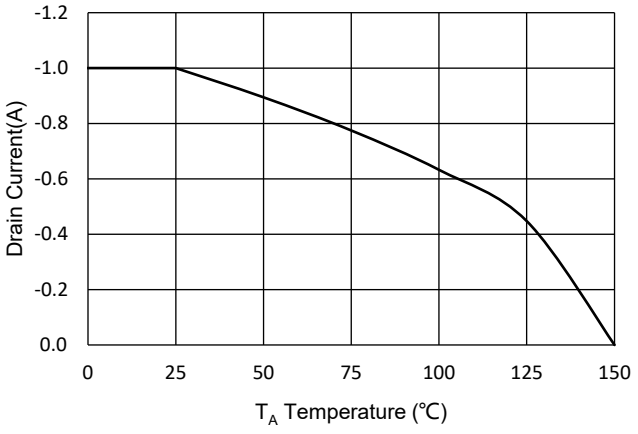
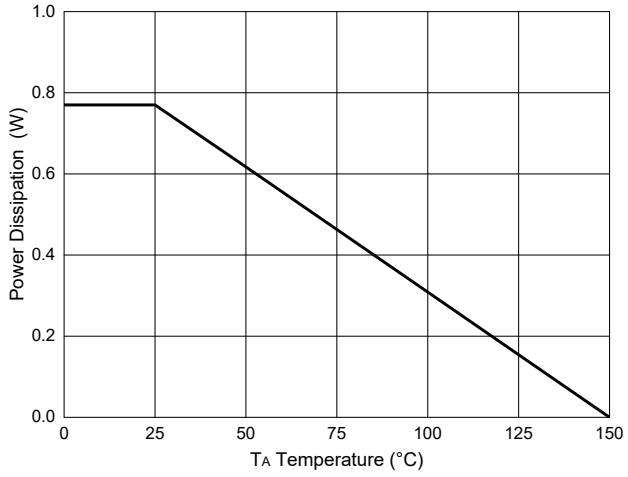


Fig.11-PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

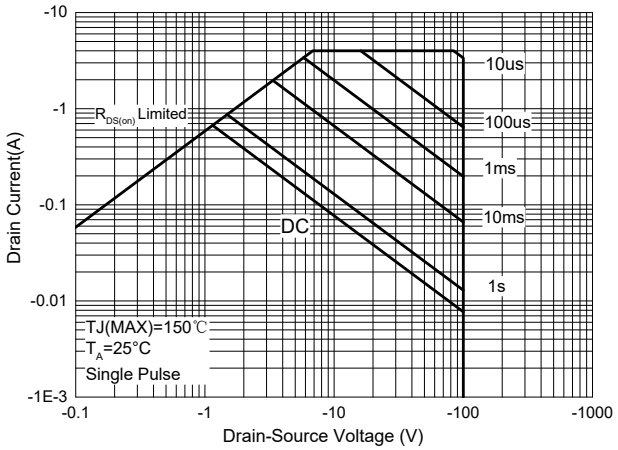
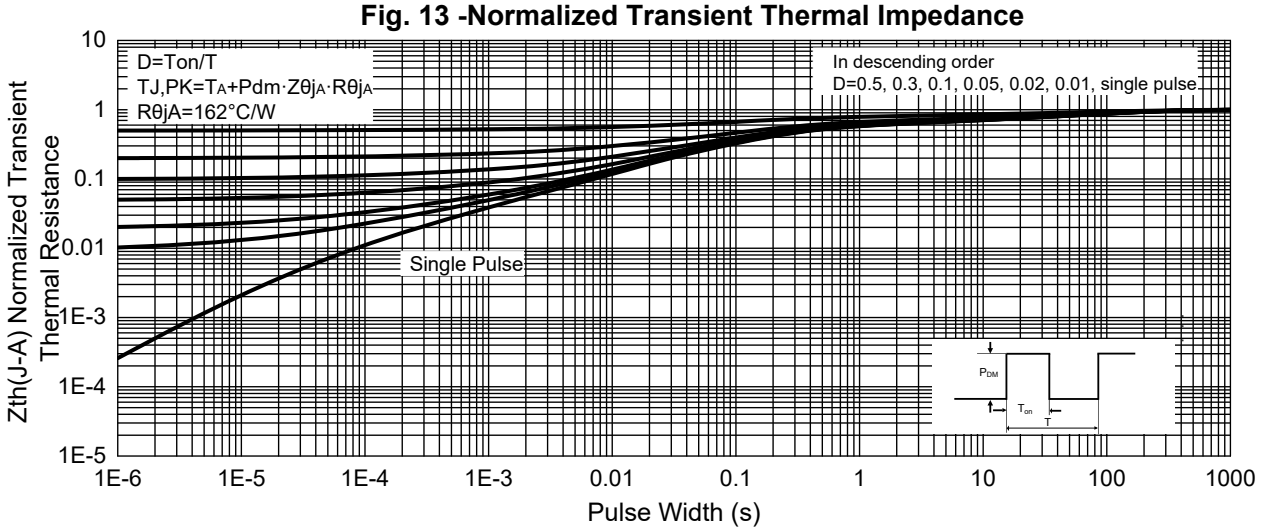


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel
Part Number-13P	Tape&Reel: 10Kpcs/Reel

For packaging details, go to our website at https://www.mccsemi.com/pdf/productpackaging/SOT-23%20Package.pdf